

### Inventor Information

Inventor One Given Name:: Mitsutoshi  
Family Name:: MIYASAKA  
Name Suffix::  
City of Residence:: Nagano  
State or Prov. of Residence::  
Country of Residence:: Japan  
Citizenship Country:: Japan

### Correspondence Information

Correspondence Customer Number:: 25944

### Application Information

Title Line One:: A METHOD FOR FORMING CRYSTALLINE  
Title Line Two:: SEMICONDUCTOR LAYERS, A METHOD FOR  
Title Line Three:: FABRICATING THIN FILM TRANSISTORS,  
Title Line Four:: AND A METHOD FOR FABRICATING SOLAR  
Title Line Five:: CELLS AND ACTIVE MATRIX LIQUID  
Title Line Six:: CRYSTAL DEVICES  
Total Drawing Sheets:: 10  
Docket Number:: 038839.02

### Continuity Information

>This application is a:: Division of  
Application One:: 09/400,303  
Filing Date:: September 21, 1999  
Patent Number::  
which is a:: Division of  
>>Application Two:: 08/776,545  
Filing Date:: January 31, 1997  
Patent Number:: 6,066,516

### Prior Foreign Applications

Foreign Application One:: 7-159147  
Filing Date:: June 26, 1995  
Country:: Japan  
Priority Claimed:: Yes  
Foreign Application Two:: 8-161280  
Filing Date:: June 21, 1996  
Country:: Japan  
Priority Claimed:: Yes

### Assignee Information

Name of assignee:: Seiko Epson Corporation  
Assignee Address Line One:: 4-1, Nishishinjuku 2-chome  
Assignee Address Line Two:: Shinjuku-ku  
City:: Tokyo

2067ED E966007

State or Province::

Country::

Postal or Zip Code::

Japan

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